Amendments to the Claims

This listing of claims will replace all prior versions, and listings of claims in the application.

Listing of Claims:

1. (currently amended) A wiring structure comprising:

an insulating layer including a groove;

a plurality of slit dummies each of which is spaced from each other in the groove; and

a wiring which is formed in the groove, the wiring having a thickness H (nm) and a width W (μm) that is larger than a <u>maximum</u> width Wmax (μm), wherein the maximum width Wmax is calculated from the following equation, Wmax = Exp (H/735);

wherein a distance L between the slit dummies is less than the maximum width Wmax.

2. (cancelled)

3. (previously presented) A wiring structure according to claim 1, wherein the slit dummies are arranged in a line and arranged along a direction in which the wiring extends.

4. (original) A wiring structure according to claim 3, wherein the slit dummies are arranged spaced equally.

5. (previously presented) A wiring structure according to claim 1, wherein the slit dummies are arranged in a plurality of lines, and wherein the slit dummies in the plurality of lines are arranged in staggered form.

6. (original) A wiring structure according to claim 5, wherein the slit dummies are arranged spaced equally.

7. (original) A wiring structure according to claim 6, wherein the slit dummies arranged in one of the lines are arranged adjacent to the edge of the wiring.

8. (previously presented) A wiring structure according to claim 1, wherein a distance between the slit dummies is approximately $\frac{\sqrt{3}}{2}$ of the maximum width Wmax.

9. (previously presented) A wiring structure according to claim 1, wherein a distance between slit dummies is approximately 85% of the maximum width Wmax.

10. (previously presented) A wiring structure according to claim 1, wherein a material of the slit dummies is the same as that of the insulating layer.

11. (original) A conductive pattern structure comprising:

a semiconductor substrate;

an insulating layer formed on the semiconductor substrate, the insulating layer having a groove;

a conductive pattern formed in the groove of the insulating layer, the conductive pattern having a thickness H (nm) and a width W (μm) that is larger than a maximum width Wmax (μm), wherein the maximum width Wmax is calculated from the equation,

$$Wmax = Exp\ (H/735);\ and$$

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a plurality of split dummies formed in entire thickness of the conductive pattern, the slit dummies being formed of an insulating material and being separated by a distance L that is less than the maximum width Wmax.

12. (original) A conductive pattern structure according to claim 11, wherein the slit dummies are arranged in a line and arranged along a direction in which the conductive pattern extends.

13. (original) A conductive pattern structure according to claim 11, wherein the slit dummies are arranged apart at equally spaced distances.

14. (original) A conductive pattern structure according to claim 11, wherein the distance between the slit dummies is approximately $\frac{\sqrt{3}}{2}$ of the maximum width Wmax.

15. (original) A conductive pattern structure according to claim 11, wherein the slit dummies are arranged in a plurality of lines, and wherein the slit dummies in the plurality of lines are arranged in staggered form.

16. (original) A conductive pattern structure according to claim 15, wherein the lines are arranged with a pitch S that is larger than the distance L.

17. (original) A conductive pattern structure according to claim 11, wherein each of the slit dummies has a substantial square form.

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18. (original) A conductive pattern structure according to claim 11, wherein a material forming the insulating layer is the same as material forming the slit dummies.